# Maria Losurdo

## List of Publications by Year in Descending Order



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|---|---|---|---|
| 158 papers | 4,012 citations | 35 h-index | 54 g-index |
| 163 ext. papers | 4,378 ext. citations | 4.8 avg, IF | 5.13 L-index |

| # | Paper | IF | Citations |
|---|---|---|---|
| 158 | Interlaboratory Study on Sb2S3 Interplay between Structure, Dielectric Function and Amorphous-to-Crystalline Phase Change for Photonics. *IScience*, **2022**, 104377 | 6.1 | 3 |
| 157 | Exploring the Thickness-Dependence of the Properties of Layered Gallium Sulfide. *Frontiers in Chemistry*, **2021**, 9, 781467 | 5 | 1 |
| 156 | Gallium Plasmonic Nanoantennas Unveiling Multiple Kinetics of Hydrogen Sensing, Storage, and Spillover. *Advanced Materials*, **2021**, 33, e2100500 | 24 | 8 |
| 155 | Gallium chiral nanoshaping for circular polarization handling. *Materials Horizons*, **2021**, 8, 187-196 | 14.4 | 5 |
| 154 | Design of Switchable On/Off Subpixels for Primary Color Generation Based on Molybdenum Oxide Gratings **2021**, 3, 655-663 | 2.1 | 0 |
| 153 | Low-Temperature and Ammonia-Free Epitaxy of the GaN/AlGaN/GaN Heterostructure. *ACS Applied Electronic Materials*, **2021**, 3, 5451-5458 | 4 | 0 |
| 152 | Nanoplasmonic Photothermal Heating and Near-Field Enhancements: A Comparative Survey of 19 Metals. *Journal of Physical Chemistry C*, **2020**, 124, 7386-7395 | 3.8 | 12 |
| 151 | Polymorphic gallium for active resonance tuning in photonic nanostructures: from bulk gallium to two-dimensional (2D) gallenene. *Nanophotonics*, **2020**, 9, 4233-4252 | 6.3 | 8 |
| 150 | Plasmonics beyond noble metals: Exploiting phase and compositional changes for manipulating plasmonic performance. *Journal of Applied Physics*, **2020**, 128, 080901 | 2.5 | 24 |
| 149 | Gallium Polymorphs: Phase-Dependent Plasmonics. *Advanced Optical Materials*, **2019**, 7, 1900307 | 8.1 | 22 |
| 148 | Optically addressing interaction of Mg/MgO plasmonic systems with hydrogen. *Optics Express*, **2019** , 27, A197-A205 | 3.3 | 8 |
| 147 | Dielectric function and plasmonic behavior of Ga(II) and Ga(III). *Optical Materials Express*, **2019**, 9, 4050 | 2.6 | 9 |
| 146 | Understanding Electromagnetic Interactions and Electron Transfer in Ga NanoparticleGrapheneMetal Substrate Sandwich Systems. *Applied Sciences (Switzerland)*, **2019**, 9, 4085 | 2.6 | 4 |
| 145 | Engineering graphene properties by modulated plasma treatments. *Carbon*, **2018**, 129, 869-877 | 10.4 | 13 |
| 144 | Thermally stable coexistence of liquid and solid phases in gallium nanoparticles. *Nature Materials*, **2016**, 15, 995-1002 | 27 | 96 |
| 143 | H2 and N2 Remote Plasma Processing of Wurtzite-Like Oxides: Implications for Energy Applications. *Plasma Processes and Polymers*, **2016**, 13, 147-160 | 3.4 | 3 |
| 142 | Morphology-controlled synthesis of NiO films: the role of the precursor and the effect of the substrate nature on the films' structural/optical properties. *RSC Advances*, **2016**, 6, 30813-30823 | 3.7 | 20 |

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| 141 | Demonstration of Improved Charge Transfer in Graphene/Au Nanorods Plasmonic Hybrids Stabilized by Benzyl Thiol Linkers. *Journal of Nanomaterials*, **2016**, 2016, 1-6 | 3.2 | 3 |
| 140 | Insights into the effects of metal nanostructuring and oxidation on the work function and charge transfer of metal/graphene hybrids. *Nanoscale*, **2015**, 7, 12868-77 | 7.7 | 29 |
| 139 | The structural properties of CdS deposited by chemical bath deposition and pulsed direct current magnetron sputtering. *Thin Solid Films*, **2015**, 582, 323-327 | 2.2 | 56 |
| 138 | In Situ Characterization of Epitaxy **2015**, 1169-1209 | | 2 |
| 137 | Gallium plasmonics: deep subwavelength spectroscopic imaging of single and interacting gallium nanoparticles. *ACS Nano*, **2015**, 9, 2049-60 | 16.7 | 93 |
| 136 | Photoactive hybrid material based on pyrene functionalized PbS nanocrystals decorating CVD monolayer graphene. *ACS Applied Materials & Interfaces*, **2015**, 7, 4151-9 | 9.5 | 27 |
| 135 | High rate deposition of thin film cadmium sulphide by pulsed direct current magnetron sputtering. *Thin Solid Films*, **2015**, 574, 43-51 | 2.2 | 25 |
| 134 | Graphene as an Electron Shuttle for Silver Deoxidation: Removing a Key Barrier to Plasmonics and Metamaterials for SERS in the Visible. *Advanced Functional Materials*, **2014**, 24, 1864-1878 | 15.6 | 77 |
| 133 | Photothermally controlled structural switching in fluorinated polyene-graphene hybrids. *Physical Chemistry Chemical Physics*, **2014**, 16, 13948-55 | 3.6 | 16 |
| 132 | Effect of Interface energy and electron transfer on shape, plasmon resonance and SERS activity of supported surfactant-free gold nanoparticles. *RSC Advances*, **2014**, 4, 29660 | 3.7 | 2 |
| 131 | Ultraviolet□Visible Plasmonic Properties of Gallium Nanoparticles Investigated by Variable-Angle Spectroscopic and Mueller Matrix Ellipsometry. *ACS Photonics*, **2014**, 1, 582-589 | 6.3 | 37 |
| 130 | Demonstrating the capability of the high-performance plasmonic gallium-graphene couple. *ACS Nano*, **2014**, 8, 3031-41 | 16.7 | 39 |
| 129 | Exploring and rationalising effective n-doping of large area CVD-graphene by NH3. *Physical Chemistry Chemical Physics*, **2014**, 16, 3632-9 | 3.6 | 40 |
| 128 | Surface plasmon resonance combined with spectroscopic ellipsometry read-out for probing surface□biomolecule interaction. *Thin Solid Films*, **2014**, 571, 478-483 | 2.2 | 2 |
| 127 | How spectroscopic ellipsometry can aid graphene technology?. *Thin Solid Films*, **2014**, 571, 389-394 | 2.2 | 15 |
| 126 | GaAs1□□PyBiz, an alternative reduced band gap alloy system lattice-matched to GaAs. *Applied Physics Letters*, **2014**, 105, 111101 | 3.4 | 21 |
| 125 | Direct Fabrication Route to Plastic-Supported Gold Nanoparticles for Flexible NIR-SERS. *Plasmonics*, **2013**, 8, 159-165 | 2.4 | 13 |
| 124 | Synthesis and characterization of plasmon resonant gold nanoparticles and graphene for photovoltaics. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2013**, 178, 559-567 | 3.1 | 20 |

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|---|---|---|---|
| 123 | Fluoro-functionalization of vinylene units in a polyarylenevinylene for polymer solar cells. *Journal of Materials Chemistry A*, **2013**, 1, 715-727 | 13 | 22 |
| 122 | The effect of atmospheric tarnishing on the optical and structural properties of silver nanoparticles. *Journal Physics D: Applied Physics*, **2013**, 46, 145308 | 3 | 35 |
| 121 | UV Plasmonic Behavior of Various Metal Nanoparticles in the Near- and Far-Field Regimes: Geometry and Substrate Effects. *Journal of Physical Chemistry C*, **2013**, 117, 19606-19615 | 3.8 | 219 |
| 120 | Real-Time Ellipsometry for Probing Charge-Transfer Processes at the Nanoscale **2013**, 453-491 | | 1 |
| 119 | Plasma-plasmonics synergy in the Ga-catalyzed growth of Si-nanowires. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2012**, 177, 700-704 | 3.1 | 4 |
| 118 | Cysteamine-based functionalization of InAs surfaces: revealing the critical role of oxide interactions in biasing attachment. *Langmuir*, **2012**, 28, 1235-45 | 4 | 14 |
| 117 | Enhancing Chemical and Optical Stability of Silver Nanostructures by Low-Temperature Hydrogen Atoms Processing. *Journal of Physical Chemistry C*, **2012**, 116, 23004-23012 | 3.8 | 14 |
| 116 | Interplay between solid-state organization and optical properties of thin films of poly-arylene-vinylene and -difluorinated vinylene: Fullerene blends. *Synthetic Metals*, **2012**, 161, 2607-2611 | 3.6 | 4 |
| 115 | Supported Faceted Gold Nanoparticles with Tunable Surface Plasmon Resonance for NIR-SERS. *Advanced Functional Materials*, **2012**, 22, 5081-5088 | 15.6 | 19 |
| 114 | Hemin-Functionalized InAs-Based High Sensitivity Room Temperature NO Gas Sensors. *Journal of Physical Chemistry C*, **2012**, 116, 826-833 | 3.8 | 16 |
| 113 | Nano- and microstructuring of graphene using UV-NIL. *Nanotechnology*, **2012**, 23, 335301 | 3.4 | 8 |
| 112 | Real-time studies of In-adlayer during PAMBE of InGaN/GaN MQWs. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 1036-1039 | | 1 |
| 111 | Evidence of plasmonic coupling in gallium nanoparticles/graphene/SiC. *Small*, **2012**, 8, 2721-30 | 11 | 33 |
| 110 | Optical properties of silicon semiconductor-supported gold nanoparticles obtained by sputtering. *Journal of Nanoscience and Nanotechnology*, **2012**, 12, 8594-9 | 1.3 | 1 |
| 109 | Ellipsometry as a Real-Time Optical Tool for Monitoring and Understanding Graphene Growth on Metals. *Journal of Physical Chemistry C*, **2011**, 115, 21804-21812 | 3.8 | 33 |
| 108 | Surface Texturing of n- and p-Doped c-Si Using a Novel Plasma Chemical Texturing Process. *Energy Procedia*, **2011**, 10, 1-7 | 2.3 | 1 |
| 107 | Graphene CVD growth on copper and nickel: role of hydrogen in kinetics and structure. *Physical Chemistry Chemical Physics*, **2011**, 13, 20836-43 | 3.6 | 324 |
| 106 | GaMg alloy nanoparticles for broadly tunable plasmonics. *Small*, **2011**, 7, 751-6 | 11 | 29 |

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| 105 | Silicon doping effect on SF6/O2 plasma chemical texturing. *Journal of Applied Physics*, **2011**, 110, 013303 | 2.5 | 2 |
| 104 | GaN/Mg Core/Shell Nanosystem for a Novel Full Color Plasmonics. *Journal of Physical Chemistry C*, **2011**, 115, 13571-13576 | 3.8 | 18 |
| 103 | Insight into Gold Nanoparticle/Hydrogen Interaction: A Way To Tailor Nanoparticle Surface Charge and Self-Assembled Monolayer Chemisorption. *Journal of Physical Chemistry C*, **2011**, 115, 19520-19528 | 3.8 | 19 |
| 102 | Applications of ellipsometry in nanoscale science: Needs, status, achievements and future challenges. *Thin Solid Films*, **2011**, 519, 2575-2583 | 2.2 | 23 |
| 101 | Interface and Surface Modification of ZnO Induced by Hydrogen and Nitrogen and their Impact on Optical Properties. *Advances in Science and Technology*, **2010**, 75, 130-135 | 0.1 | |
| 100 | A two-step plasma processing for gold nanoparticles supported on silicon near-infrared plasmonics. *Applied Physics Letters*, **2010**, 96, 043104 | 3.4 | 22 |
| 99 | Tailoring Optical Properties of Blue-Gap Poly(p-phenylene Vinylene)s for LEDs Applications. *Advances in Science and Technology*, **2010**, 75, 118-123 | 0.1 | |
| 98 | Advanced Real Time Metrology of AlGaN/GaN and InGaN/GaN Epitaxy. *Advances in Science and Technology*, **2010**, 75, 124-129 | 0.1 | |
| 97 | Size dependence of the dielectric function of silicon-supported plasmonic gold nanoparticles. *Physical Review B*, **2010**, 82, | 3.3 | 35 |
| 96 | Tailoring density and optical and thermal behavior of gold surfaces and nanoparticles exploiting aromatic dithiols. *Langmuir*, **2010**, 26, 8430-40 | 4 | 39 |
| 95 | Fluorinated Poly(p-phenylenevinylene)s: Synthesis and Optical Properties of an Intriguing Class of Luminescent Polymers. *Materials*, **2010**, 3, 3077-3091 | 3.5 | 25 |
| 94 | Adsorption and desorption kinetics of Ga on GaN(0001): Application of Wolkenstein theory. *Physical Review B*, **2010**, 82, | 3.3 | 6 |
| 93 | Synthesis and characterization of perfluorinated arylenevinylene polymers. *Journal of Polymer Science Part A*, **2010**, 48, 285-291 | 2.5 | 15 |
| 92 | Real time monitoring of the interaction of Si (100) with atomic hydrogen: The H-insertion/Si-etching kinetic model explaining Si surface modifications. *Applied Physics Letters*, **2009**, 95, 161501 | 3.4 | 9 |
| 91 | Band bending and adsorption/desorption kinetics on N-polar GaN surfaces. *Journal of Vacuum Science & Technology B*, **2009**, 27, 107 | | 10 |
| 90 | Optical and Electronic NO(x) Sensors for Applications in Mechatronics. *Sensors*, **2009**, 9, 3337-56 | 3.8 | 21 |
| 89 | Blue-Gap Poly(p-phenylene vinylene)s with Fluorinated Double Bonds: Interplay Between Supramolecular Organization and Optical Properties in Thin Films. *Advanced Materials*, **2009**, 21, 1115-1120 | 24 | 44 |
| 88 | Is There a ZnO Face Stable to Atomic Hydrogen?. *Advanced Materials*, **2009**, 21, 1700-1706 | 24 | 52 |

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| 87 | Structural, Optical, and Electrical Characterization of ZnO and Al-doped ZnO Thin Films Deposited by MOCVD. *Chemical Vapor Deposition*, **2009**, 15, n/a-n/a | | 7 |
| 86 | Metalorganic chemical vapor deposition of Er2O3 thin films: Correlation between growth process and film properties. *Thin Solid Films*, **2009**, 517, 2606-2610 | 2.2 | 5 |
| 85 | Role of plasma activation in tailoring the nanostructure of multifunctional oxides thin films. *Applied Surface Science*, **2009**, 255, 5396-5400 | 6.7 | 1 |
| 84 | Spectroscopic ellipsometry and polarimetry for materials and systems analysis at the nanometer scale: state-of-the-art, potential, and perspectives. *Journal of Nanoparticle Research*, **2009**, 11, 1521-1554 | 2.3 | 155 |
| 83 | Enhanced absorption in Au nanoparticles/a-Si:H/c-Si heterojunction solar cells exploiting Au surface plasmon resonance. *Solar Energy Materials and Solar Cells*, **2009**, 93, 1749-1754 | 6.4 | 72 |
| 82 | Demonstration of surface-enhanced Raman scattering by tunable, plasmonic gallium nanoparticles. *Journal of the American Chemical Society*, **2009**, 131, 12032-3 | 16.4 | 71 |
| 81 | InAs(100) Surfaces Cleaning by an As-Free Low-Temperature 100°C Treatment. *Journal of the Electrochemical Society*, **2009**, 156, H263 | 3.9 | 11 |
| 80 | From amorphous to microcrystalline silicon: Moving from one to the other by halogenated silicon plasma chemistry. *Philosophical Magazine*, **2009**, 89, 2469-2489 | 1.6 | 5 |
| 79 | Plasmonic gallium nanoparticles on polar semiconductors: interplay between nanoparticle wetting, localized surface plasmon dynamics, and interface charge. *Langmuir*, **2009**, 25, 924-30 | 4 | 50 |
| 78 | Relationship between Nanostructure and Optical Properties of ZnO Thin Films. *Journal of Physical Chemistry C*, **2008**, 112, 9595-9599 | 3.8 | 39 |
| 77 | Tailoring nanostructure of ZnO thin films by plasma assisted and Au-catalyst assisted MOCVD. *Journal of Non-Crystalline Solids*, **2008**, 354, 2821-2825 | 3.9 | 3 |
| 76 | Characterization of chromium silicide thin layer formed on amorphous silicon films. *Journal of Non-Crystalline Solids*, **2008**, 354, 2171-2175 | 3.9 | 17 |
| 75 | Correlation between structure and properties of Er2O3 nanocrystalline thin films. *Journal of Non-Crystalline Solids*, **2008**, 354, 2853-2857 | 3.9 | 8 |
| 74 | Lanthanum Oxyfluoride Sol□gel Thin Films by a Simple Single-Source Precursor Route. *Journal of Physical Chemistry C*, **2008**, 112, 14508-14512 | 3.8 | 17 |
| 73 | Structural and Optical Properties of Nanocrystalline Er[sub 2]O[sub 3] Thin Films Deposited by a Versatile Low-Pressure MOCVD Approach. *Journal of the Electrochemical Society*, **2008**, 155, G44 | 3.9 | 17 |
| 72 | Interplay between surface chemistry and optical behavior of semiconductor-biomolecule functionalized sensing systems: an optical investigation by spectroscopic ellipsometry. *Materials Research Society Symposia Proceedings*, **2008**, 1133, 1 | | 1 |
| 71 | Indium adlayer kinetics on the gallium nitride (0001) surface: Monitoring indium segregation and precursor-mediated adsorption. *Physical Review B*, **2008**, 77, | 3.3 | 32 |
| 70 | Impact of fluorinated vinylene units on supramolecular organization and optical properties of poly(p-phenylenedifluorovinylene) thin films as a class of blue band gap conjugated polymers. *Polymer*, **2008**, 49, 4133-4140 | 3.9 | 24 |

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| 69 | Multifunctional Nanocrystalline Thin Films of Er2O3: Interplay between Nucleation Kinetics and Film Characteristics. *Advanced Functional Materials*, **2007**, 17, 3607-3612 | 15.6 | 21 |
| 68 | Insight into excimer laser crystallization exploiting ellipsometry: Effect of silicon film precursor. *Thin Solid Films*, **2007**, 515, 7508-7512 | 2.2 | 4 |
| 67 | III-Nitrides growth and AlGaN/GaN heterostructures on ferroelectric materials. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2007**, 140, 203-211 | 3.1 | 7 |
| 66 | In situ spectroscopic ellipsometry to monitor surface plasmon resonant group-III metals deposited by molecular beam epitaxy. *Journal of Vacuum Science & Technology B*, **2007**, 25, 1019 | | 21 |
| 65 | Kinetics of gallium adlayer adsorption/desorption on polar and nonpolar GaN surfaces. *Journal of Vacuum Science & Technology B*, **2007**, 25, 969 | | 21 |
| 64 | Real time optical monitoring of molecular beam epitaxy of InN on SiC substrates. *Journal of Vacuum Science & Technology B*, **2007**, 25, 1014 | | 2 |
| 63 | Plasma ehnancement of metalorganic chemical vapor deposition and properties of Er2O3 nanostructured thin films. *Applied Physics Letters*, **2007**, 91, 061923 | 3.4 | 6 |
| 62 | Functionalization and characterization of InAs and InP surfaces with hemin. *Journal of Vacuum Science & Technology B*, **2007**, 25, 1504 | | 18 |
| 61 | Real-time plasmon resonance tuning of liquid Ga nanoparticles by in situ spectroscopic ellipsometry. *Applied Physics Letters*, **2007**, 90, 103119 | 3.4 | 80 |
| 60 | MOCVD Template Approach to the Fabrication of Free-Standing Nickel(II) Oxide Nanotube Arrays: Structural, Morphological, and Optical Properties Characterization. *Journal of Physical Chemistry C*, **2007**, 111, 3211-3215 | 3.8 | 42 |
| 59 | Behavior of hydrogen in InN investigated in real time exploiting spectroscopic ellipsometry. *Applied Physics Letters*, **2007**, 91, 081917 | 3.4 | 8 |
| 58 | Er2O3 as a high-K dielectric candidate. *Applied Physics Letters*, **2007**, 91, 091914 | 3.4 | 44 |
| 57 | Characteristics of InN grown on SiC under the In-rich regime by molecular beam heteroepitaxy. *Applied Physics Letters*, **2007**, 90, 011910 | 3.4 | 14 |
| 56 | III-nitride growth and characteristics on ferroelectric materials using plasma-assisted molecular beam epitaxy. *Journal of Vacuum Science & Technology B*, **2006**, 24, 2093 | | 8 |
| 55 | Effect of the Matrix on the 1.5μm Photoluminescence of Er-Doped Silicon Quantum Dots. *Materials Science Forum*, **2006**, 514-516, 1116-1120 | 0.4 | 1 |
| 54 | Plasma-assisted metalorganic chemical vapor deposition growth of ZnO thin films. *Journal of Materials Research*, **2006**, 21, 1632-1637 | 2.5 | 16 |
| 53 | Kinetics of gallium adsorption and desorption on (0001) gallium nitride surfaces. *Applied Physics Letters*, **2006**, 89, 181915 | 3.4 | 14 |
| 52 | Fundamental reactions controlling anion exchange during mixed anion heterojunction formation: Chemistry and kinetics of P-for-As exchange reaction. *Journal of Applied Physics*, **2006**, 99, 093510 | 2.5 | 5 |

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| 51 | Surface oxide relationships to band bending in GaN. *Applied Physics Letters*, **2006**, 88, 013506 | 3.4 | 42 |
| 50 | Study of the dielectric function of hexagonal InN: Impact of indium clusters and of native oxide. *Applied Physics Letters*, **2006**, 88, 121928 | 3.4 | 19 |
| 49 | Dielectric function and electric properties of germanium thin films prepared by gold mediated crystallization. *Journal of Applied Physics*, **2006**, 99, 063511 | 2.5 | 16 |
| 48 | Impact of 4H- and 6H-SiC(0001) nitridation on Ga wetting layer development and GaN growth by molecular beam epitaxy. *Applied Physics Letters*, **2006**, 89, 021916 | 3.4 | 5 |
| 47 | Fundamental reactions controlling anion exchange during mixed anion heterojunction formation: Chemistry of As-for-Sb and Sb-for-As exchange reactions. *Journal of Applied Physics*, **2006**, 100, 013531 | 2.5 | 39 |
| 46 | Calcium copper-titanate thin film growth: tailoring of the operational conditions through nanocharacterization and substrate nature effects. *Journal of Physical Chemistry B*, **2006**, 110, 17460-7 | 3.4 | 30 |
| 45 | Amorphous Silicon Nitride: a suitable alloy for optical multilayered structures. *Journal of Non-Crystalline Solids*, **2006**, 352, 1294-1297 | 3.9 | 22 |
| 44 | Growth of InN on 6H-SiC by plasma assisted molecular beam epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1531-1535 | | 3 |
| 43 | Real time spectroscopic ellipsometry investigation of homoepitaxial GaN grown by plasma assisted molecular beam epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1583-1586 | | 1 |
| 42 | Buffer free MOCVD growth of GaN on 4H-SiC: Effect of substrate treatments and UV-photoirradiation. *Physica Status Solidi (A) Applications and Materials Science*, **2006**, 203, 1607-1611 | 1.6 | 4 |
| 41 | Real time ellipsometry for monitoring plasma-assisted epitaxial growth of GaN. *Applied Surface Science*, **2006**, 253, 219-223 | 6.7 | 4 |
| 40 | Structural-optical study of high-dielectric-constant oxide films. *Applied Surface Science*, **2006**, 253, 322-326 | 6.7 | 24 |
| 39 | Plasma processing of the Si(0 0 1) surface for tuning SPR of Au/Si-based plasmonic nanostructures. *Journal of Luminescence*, **2006**, 121, 322-326 | 3.8 | 13 |
| 38 | Optical and electrical properties of nanostructured LaCoO3 thin films. *Applied Physics Letters*, **2005**, 87, 061909 | 3.4 | 11 |
| 37 | Recent advances in characterization of CaCu3Ti4O12 thin films by spectroscopic ellipsometric metrology. *Journal of the American Chemical Society*, **2005**, 127, 13772-3 | 16.4 | 25 |
| 36 | Structural and optical investigation of plasma deposited silicon carbon alloys: Insights on Si-C bond configuration using spectroscopic ellipsometry. *Journal of Applied Physics*, **2005**, 97, 103504 | 2.5 | 31 |
| 35 | Nucleation and growth mode of the molecular beam epitaxy of GaN on 4H-SiC exploiting real time spectroscopic ellipsometry. *Journal of Crystal Growth*, **2005**, 284, 156-165 | 1.6 | 11 |
| 34 | RF-sputtering of gold on silica surfaces: Evolution from clusters to continuous films. *Materials Science and Engineering C*, **2005**, 25, 599-603 | 8.3 | 28 |

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| 33 | A study of remote plasma nitrided nGaAs/Au Schottky barrier. *Solid-State Electronics*, **2005**, 49, 413-419 | 1.7 | 14 |
| 32 | Modification of 4H-SiC and 6H-SiC(0001)Si surfaces through the interaction with atomic hydrogen and nitrogen. *Journal of Electronic Materials*, **2005**, 34, 457-465 | 1.9 | 10 |
| 31 | Impact of unintentional and intentional nitridation of the 6H-SiC(0001)Si substrate on GaN epitaxy. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2005**, 23, 1181 | | 2 |
| 30 | Interaction of atomic hydrogen with Zn-polar and O-polar ZnO surfaces. *Applied Physics Letters*, **2005**, 86, 091901 | 3.4 | 35 |
| 29 | III-nitrides on oxygen- and zinc-face ZnO substrates. *Applied Physics Letters*, **2005**, 87, 184104 | 3.4 | 27 |
| 28 | Interfacial reactions during GaN and AiN epitaxy on 4H□and 6H□iC(0001). *Applied Physics Letters*, **2005**, 86, 021920 | 3.4 | 11 |
| 27 | Modification of InN Properties by Interactions with Hydrogen and Nitrogen. *Materials Research Society Symposia Proceedings*, **2005**, 892, 137 | | |
| 26 | Fundamental reactions controlling anion exchange during the synthesis of Sb/As mixed-anion heterojunctions. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2004**, 22, 2244 | | 7 |
| 25 | Interplay between GaN polarity and surface reactivity towards atomic hydrogen. *Journal of Applied Physics*, **2004**, 95, 8408-8418 | 2.5 | 22 |
| 24 | Influence of process parameters on the morphology of Au□iO2 nanocomposites synthesized by radio-frequency sputtering. *Journal of Applied Physics*, **2004**, 96, 1655-1665 | 2.5 | 54 |
| 23 | Study of the temperature-dependent interaction of 4H□iC and 6H□iC surfaces with atomic hydrogen. *Applied Physics Letters*, **2004**, 84, 4011-4013 | 3.4 | 18 |
| 22 | Relationships among surface processing at the nanometer scale, nanostructure and optical properties of thin oxide films. *Thin Solid Films*, **2004**, 455-456, 301-312 | 2.2 | 37 |
| 21 | The surface modification and reactivity of LiGaO2 substrates during GaN epitaxy. *Journal of Crystal Growth*, **2004**, 264, 139-149 | 1.6 | 11 |
| 20 | Study of the interaction of 4H□iC and 6H□iC(0001)Si surfaces with atomic nitrogen. *Applied Physics Letters*, **2004**, 85, 4034-4036 | 3.4 | 21 |
| 19 | Relationship between the Nanostructures and the Optical Properties of CeO2 Thin Films. *Journal of Physical Chemistry B*, **2004**, 108, 16357-16364 | 3.4 | 28 |
| 18 | Nanostructure and optical properties of CeO2 thin films obtained by plasma-enhanced chemical vapor deposition. *Materials Science and Engineering C*, **2003**, 23, 1013-1016 | 8.3 | 53 |
| 17 | Optimization of ITO layers for applications in a-Si/c-Si heterojunction solar cells. *Thin Solid Films*, **2003**, 425, 185-192 | 2.2 | 74 |
| 16 | Morphology, structure and optical properties of sol□el ITO thin films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2003**, 101, 222-226 | 3.1 | 31 |

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| 15 | The impact of substrate nitridation temperature and buffer design and synthesis on the polarity of GaN epitaxial films. *Journal of Crystal Growth*, **2003**, 252, 159-166 | 1.6 | 31 |
| 14 | Study of Anisotropic Optical Properties of Poly(arylenephenylene) Thin Films: Dependence on Polymer Backbone. *Macromolecules*, **2003**, 36, 4492-4497 | 5.5 | 20 |
| 13 | Dielectric function of nanocrystalline silicon with few nanometers (. *Applied Physics Letters*, **2003**, 82, 2993-2995 | 3.4 | 56 |
| 12 | Spectroscopic ellipsometry for characterization of organic semiconductor polymeric thin films. *Synthetic Metals*, **2003**, 138, 49-53 | 3.6 | 21 |
| 11 | Anisotropy of optical properties of conjugated polymer thin films by spectroscopic ellipsometry. *Journal of Applied Physics*, **2003**, 94, 4923 | 2.5 | 34 |
| 10 | A Chemical Perspective of GaN Polarity: The use of Hydrogen Plasma Dry Etching Versus NaOH Wet Etching to Determine Polarity. *Materials Research Society Symposia Proceedings*, **2002**, 722, 341 | | 3 |
| 9 | Wet chemical nitridation of GaAs (100) by hydrazine solution for surface passivation. *Applied Physics Letters*, **2002**, 80, 3739-3741 | 3.4 | 45 |
| 8 | Role of low-temperature (200 °C) nitridation in the growth of GaN by plasma-assisted molecular-beam epitaxy. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2002**, 20, 1221 | | 16 |
| 7 | Role of sapphire nitridation temperature on GaN growth by plasma assisted molecular beam epitaxy: Part I. Impact of the nitridation chemistry on material characteristics. *Journal of Applied Physics*, **2002**, 91, 2499-2507 | 2.5 | 78 |
| 6 | Role of sapphire nitridation temperature on GaN growth by plasma assisted molecular beam epitaxy: Part II. Interplay between chemistry and structure of layers. *Journal of Applied Physics*, **2002**, 91, 2508-2518 | 2.5 | 46 |
| 5 | N2H2 remote plasma nitridation for GaAs surface passivation. *Applied Physics Letters*, **2002**, 81, 16-18 | 3.4 | 39 |
| 4 | Spectroscopic ellipsometry investigation of V2O5 nanocrystalline thin films. *Thin Solid Films*, **2001**, 384, 58-64 | 2.2 | 37 |
| 3 | Dielectric function of V2O5 nanocrystalline films by spectroscopic ellipsometry: Characterization of microstructure. *Applied Physics Letters*, **2000**, 77, 1129-1131 | 3.4 | 28 |
| 2 | Time-resolved optical emission spectroscopy of modulated plasmas for amorphous silicon deposition. *Plasma Sources Science and Technology*, **1992**, 1, 156-165 | 3.5 | 27 |
| 1 | Polarimetry Analysis and Optical Contrast of Sb Phase Change Material. *Optical Materials Express*, | 2.6 | 4 |